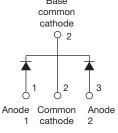
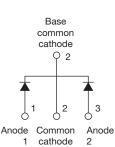


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Ultrafast Rectifier, 2 x 5 A FRED Pt[®]







TO-262AA

VS-MURB1020CTPbF

VS-MURB1020CT-1PbF

PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK), TO-262AA					
I _{F(AV)}	2 x 5 A					
V _R	200 V					
V _F at I _F	0.87 V					
t _{rr}	25 ns					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C HALOGEN FREE
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200	V			
Average reatified forward average p		I		5				
Average rectified forward current total de	total device	I _{F(AV)}	Rated V _R , T _C = 149 °C	10	А			
Non-repetitive peak surge current per leg		I _{FSM}		50	A			
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 149 °C	10				
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward voltage	V _F	I _F = 5 A, T _J = 25 °C	-	0.99	1.08	v		
		I _F = 5 A, T _J = 125 °C	-	0.87	0.99			
		I _F = 10 A, T _J = 25 °C	-	1.12	1.25			
		I _F = 10 A, T _J = 125 °C	-	1.02	1.20			
	I _R	$V_{\rm R} = V_{\rm R}$ rated	-	-	10			
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA		
Junction capacitance	CT	V _R = 200 V	-	8	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

Revision: 02-Feb-16

Document Number: 94518

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/μs, V _R = 30 V	-	-	35		
	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ V}$		-	-	25		
		T _J = 25 °C		-	24	-	ns	
		T _J = 125 °C		-	35	-		
Deals receivers aurrent	1	T _J = 25 °C	$I_F = 5 A$	-	3.3	-	٨	
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 200 A/μs V _R = 160 V	-	5.0	-	A	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	33	-		
		T _J = 125 °C		-	76	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5		
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
W/oight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking davias		Case style TO-263AB (D ² PAK)	MURB1020CT				
Marking device		Case style TO-262		MURB1020CT-1			



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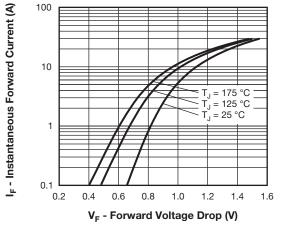
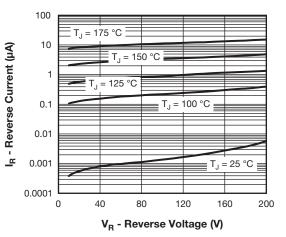
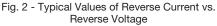


Fig. 1 - Typical Forward Voltage Drop Characteristics





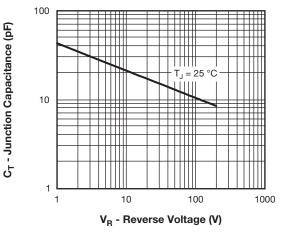


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

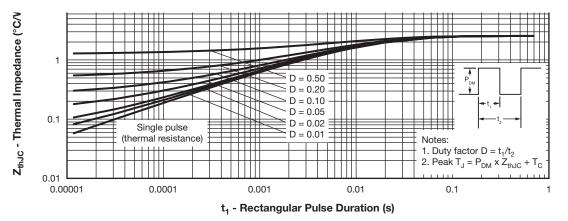
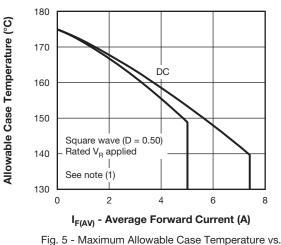


Fig. 4 - Maximum Thermal Impedance $\mathsf{Z}_{\mathsf{thJC}}$ Characteristics

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Average Forward Current

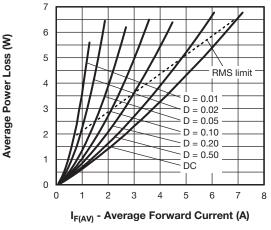
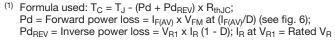


Fig. 6 - Forward Power Loss Characteristics

Note



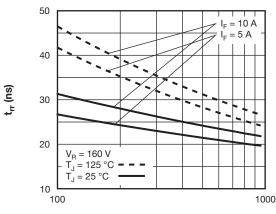




Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

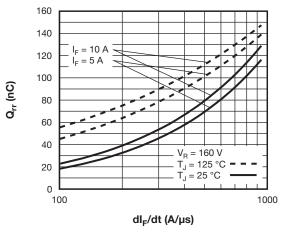


Fig. 8 - Typical Stored Charge vs. dl_F/dt



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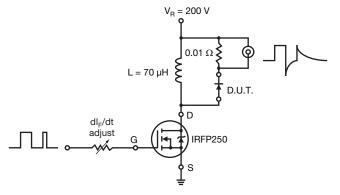


Fig. 9 - Reverse Recovery Parameter Test Circuit

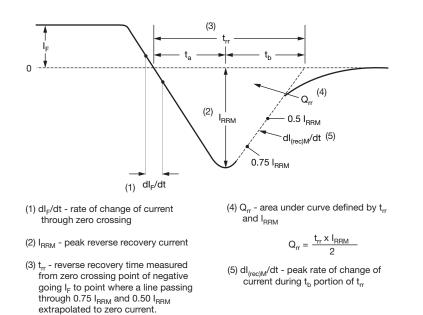


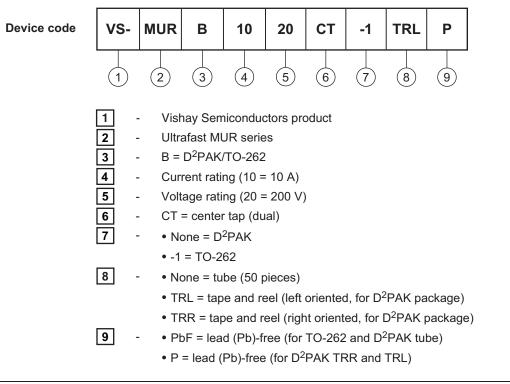
Fig. 10 - Reverse Recovery Waveform and Definitions

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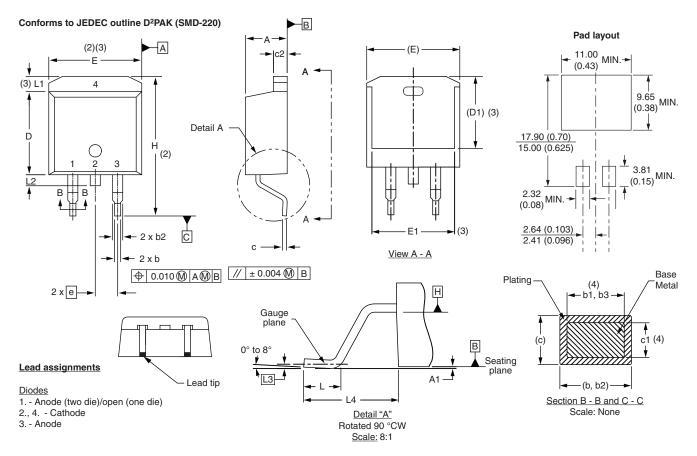
ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95014						
Part marking information	www.vishay.com/doc?95008						
Packaging information	www.vishay.com/doc?95032						

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D²PAK, TO-262



DIMENSIONS - D²PAK in millimeters and inches

SHA

SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
с	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

CVMDOI			NOTES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	
L4	4.70	5.20	0.100	0.200	

INCHES

NOTES

MILLIMETERS

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

- ⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1
- ⁽⁴⁾ Dimension b1 and c1 apply to base metal only
- ⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

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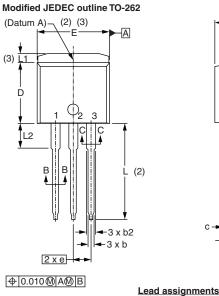
Outline Dimensions

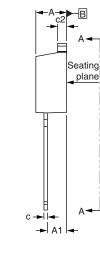
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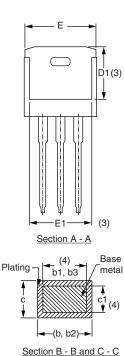
D²PAK, TO-262



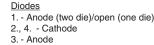
DIMENSIONS - TO-262 in millimeters and inches

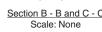






Lead tip





(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the

actual package outline

SYMBOL	MILLIMETERS		INC	NOTES	
STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	- 0.065		3
L2	3.56	3.71	0.140	0.146	

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- ⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1
- ⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

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